



STS8DNF3LL

Dual N-channel 30V - 0.017Ω - 8A SO-8
Low gate charge STripFET™ II Power MOSFET

General features

| Type | V _{DSS} | R _{DS(on)} | I _D |
|------------|------------------|---------------------|----------------|
| STS8DNF3LL | 30V | <0.020Ω | 8A |

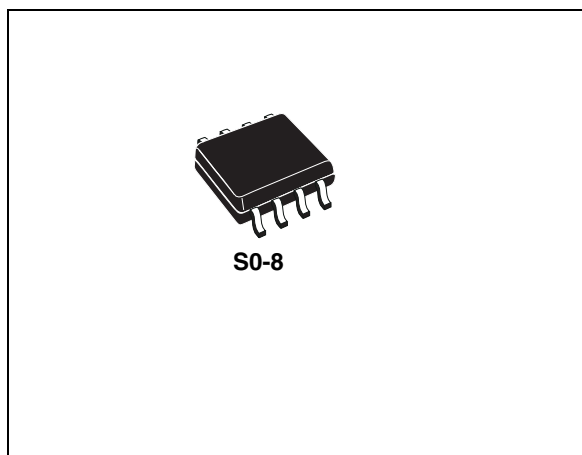
- Optimal R_{DS(on)} x Q_g trade-off @ 4.5V
- Conduction losses reduced
- Switching losses reduced

Description

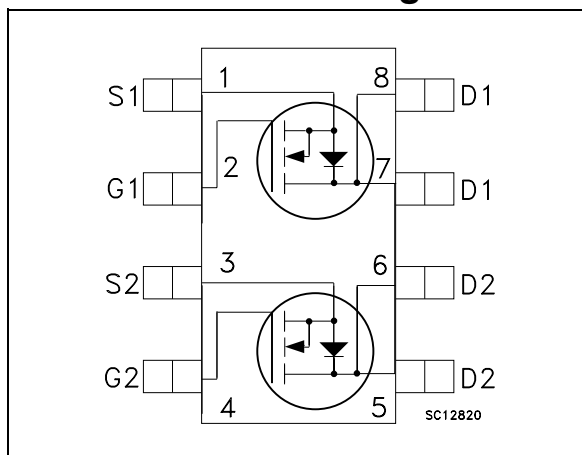
This application specific Power MOSFET is the second generation of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows the best trade-off between on-resistance and gate charge. When used as high and low side in buck regulators, it gives the best performance in terms of both conduction and switching losses. This is extremely important for motherboards where fast switching and high efficiency are of paramount importance.

Applications

- Switching application



Internal schematic diagram



Order codes

| Part number | Marking | Package | Packaging |
|-------------|----------|---------|-------------|
| STS8DNF3LL | S8DNF3LL | SO-8 | Tape & reel |

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1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|----------|------|
| V_{DS} | Drain-source voltage ($v_{gs} = 0$) | 30 | V |
| V_{GS} | Gate- source voltage | ± 16 | V |
| I_D | Drain current (continuous) at $T_C = 25^\circ\text{C}$ single operating | 8 | A |
| I_D | Drain current (continuous) at $T_C = 100^\circ\text{C}$ single operating | 5 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 32 | A |
| P_{TOT} | Total dissipation at $T_C = 25^\circ\text{C}$ dual operating | 2 | W |
| | Total dissipation at $T_C = 25^\circ\text{C}$ single operating | 1.6 | W |

1. Pulse width limited by safe operating area

Table 2. Thermal data

| | | | |
|-------------|--|------------|---------------------------|
| R_{thj-a} | ⁽¹⁾ Thermal resistance junction-ambient single operating | 78 | $^\circ\text{C}/\text{W}$ |
| | Thermal resistance junction-ambient dual operating | 62.5 | $^\circ\text{C}/\text{W}$ |
| T_J | Thermal operating junction-ambient | 150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | -55 to 150 | $^\circ\text{C}$ |

1. Mounted on FR-4 board with 0.5 in² pad of Cu.

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|---|---|------|-------|-----------|----------|
| $V_{(BR)DSS}$ | Drain-source Breakdown voltage | $I_D = 250 \mu A, V_{GS} = 0$ | 30 | | | V |
| I_{DSS} | Zero gate voltage | $V_{DS} = \text{Max rating}$ | | | 1 | μA |
| | Drain current ($V_{GS} = 0$) | $V_{DS} = \text{Max rating},$ $T_C = 125^{\circ}C$ | | | 10 | μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 16V$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 1 | | | V |
| $R_{DS(on)}$ | Static drain-source on resistance | $V_{GS} = 10V, I_D = 4A$ | | 0.017 | 0.020 | Ω |
| | | $V_{GS} = 4.5V, I_D = 4A$ | | 0.020 | 0.024 | Ω |

Table 4. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------|---------------------------------|---|------|------|------|------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 15V, I_D = 4 A$ | | 12.5 | | S |
| C_{iss} | Input capacitance | $V_{DS} = 25V, f = 1 \text{ MHz},$ $V_{GS} = 0$ | | 800 | | pF |
| C_{oss} | Output capacitance | | | 250 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 60 | | pF |
| Q_g | Total gate charge | $V_{DD} = 15V, I_D = 8A,$ $V_{GS} = 5V$ (see Figure 14) | | 12.5 | 17 | nC |
| Q_{gs} | Gate-source charge | | | 3.2 | | nC |
| Q_{gd} | Gate-drain charge | | | 4.5 | | nC |

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5.

Table 5. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------|---------------------|---|---|------|------|------|
| $t_{d(on)}$ t_r | Turn-on delay time | $V_{DD} = 15 V, I_D = 4A,$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ (see Figure 13) | | 18 | | ns |
| | Rise time | | | 32 | | ns |
| $t_{d(off)}$ t_f | Turn-off Delay Time | | $V_{DD} = 15 V, I_D = 4A,$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ (see Figure 13) | | 21 | |
| | Fall Time | | | 11 | | ns |

Table 6. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max | Unit |
|-----------------|-------------------------------|--|------|------|-----|------|
| I_{SD} | Source-drain current | | | | 8 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | | | 32 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 8A, V_{GS} = 0$ | | | 1.2 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 8A, V_{DD} = 15V$ $di/dt = 100A/\mu s,$ $T_j = 150^\circ C$ (see Figure 15) | | 23 | | ns |
| Q_{rr} | Reverse recovery charge | | | 17 | | nC |
| I_{RRM} | Reverse recovery current | | | 1.5 | | A |

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

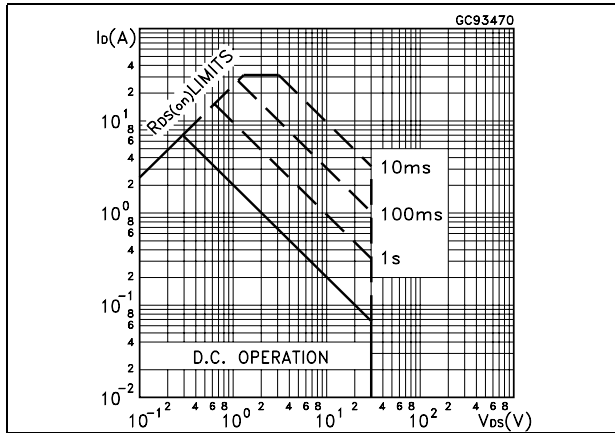


Figure 2. Thermal impedance

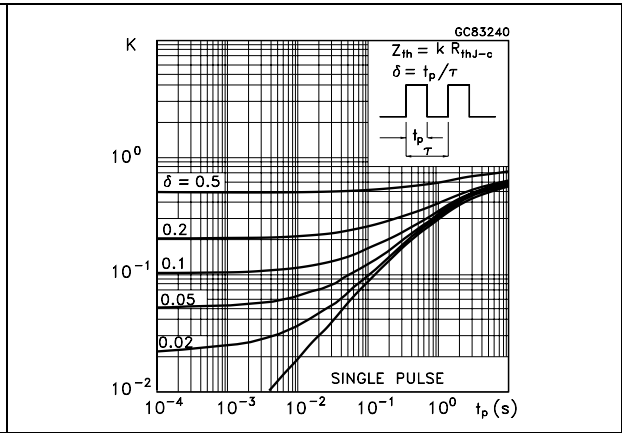


Figure 3. Output characteristics

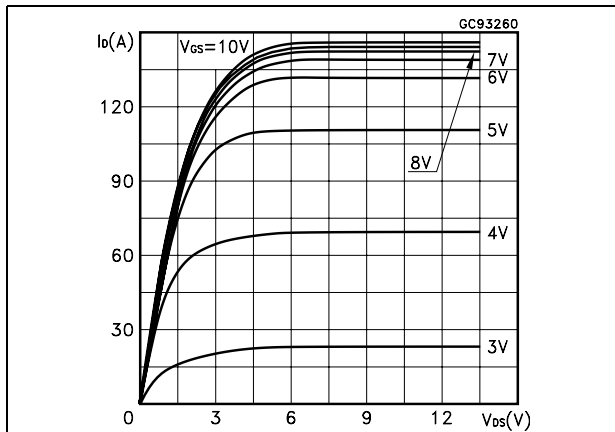


Figure 4. Transfer characteristics

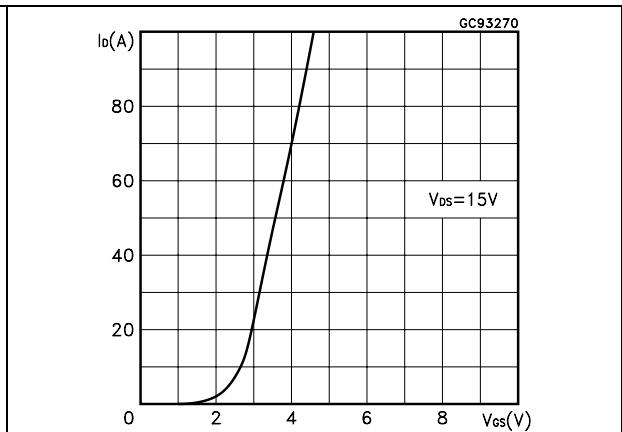


Figure 5. Transconductance

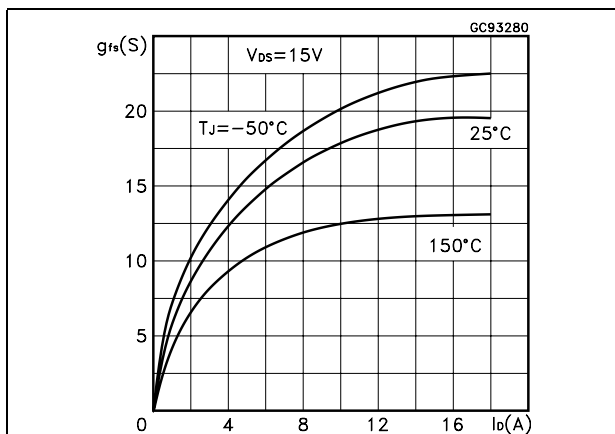


Figure 6. Static drain-source on resistance

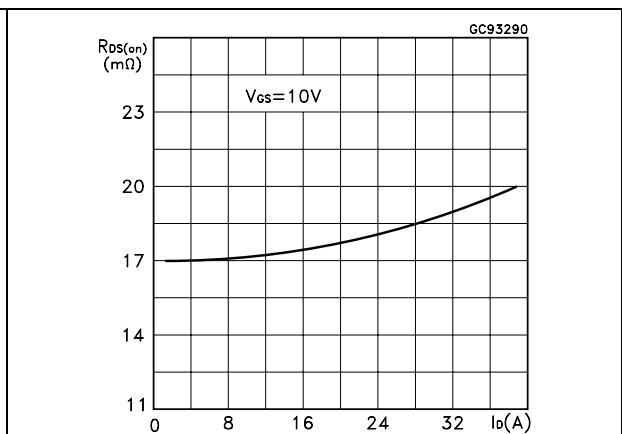


Figure 7. Gate charge vs. gate-source voltage Figure 8. Capacitance variations

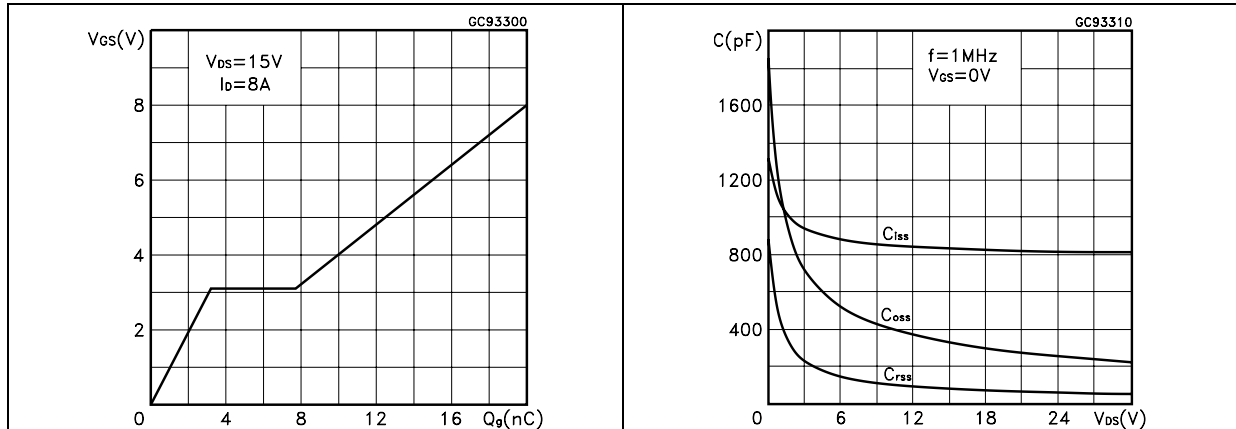


Figure 9. Normalized gate threshold voltage vs. temperature Figure 10. Normalized on resistance vs. temperature

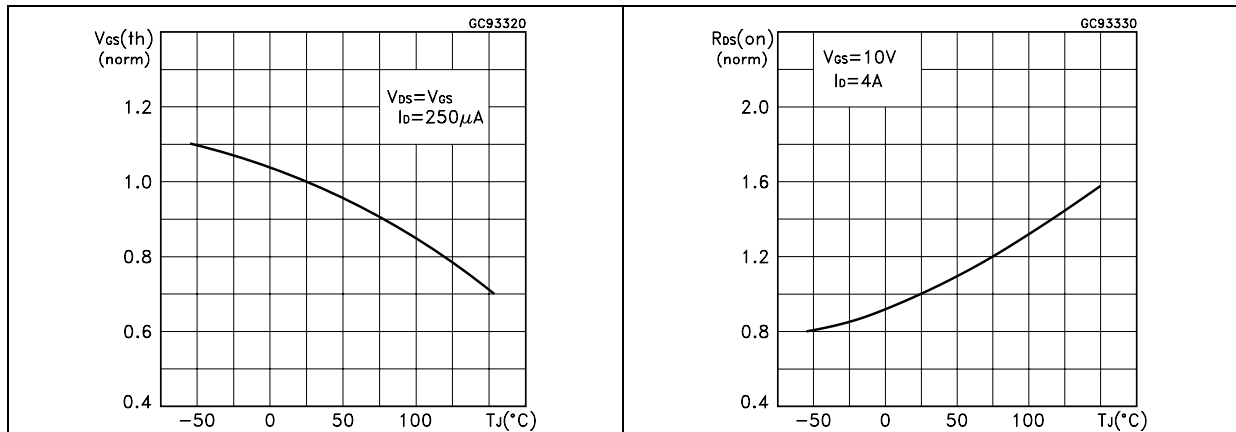
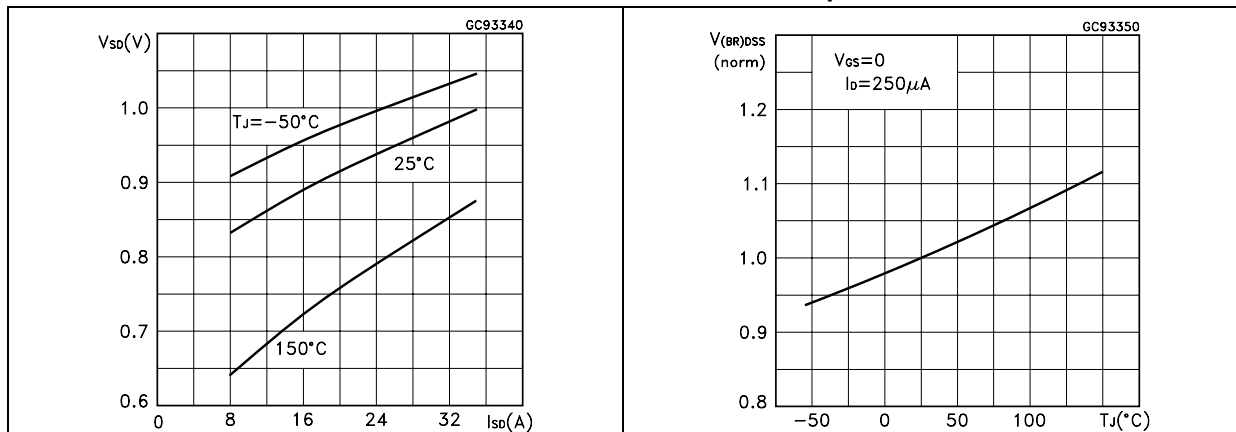


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized breakdown voltage vs. temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

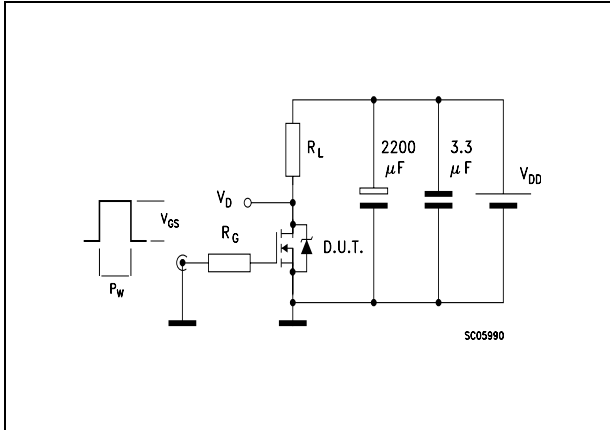


Figure 14. Gate charge test circuit

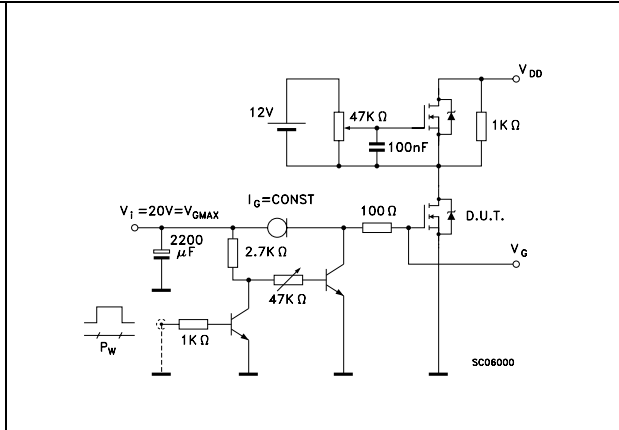


Figure 15. Test circuit for inductive load switching and diode recovery times

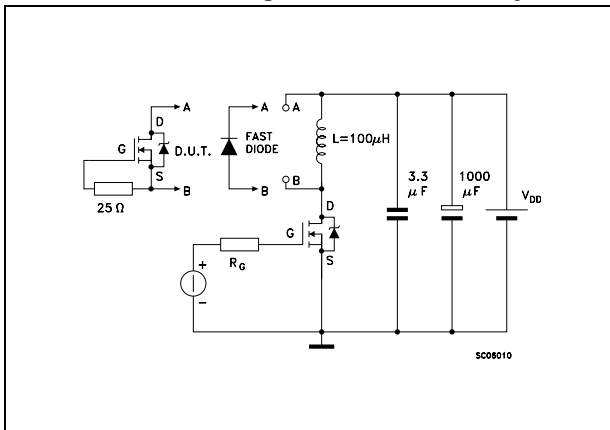


Figure 16. Unclamped Inductive load test circuit

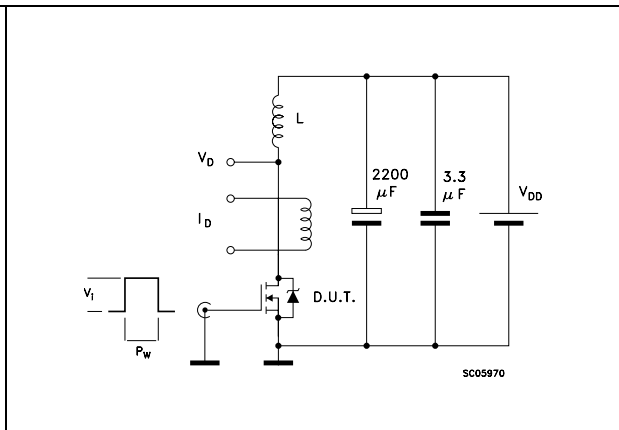


Figure 17. Unclamped inductive waveform

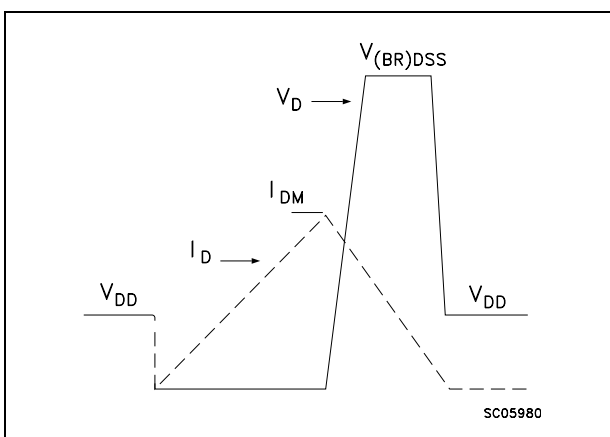
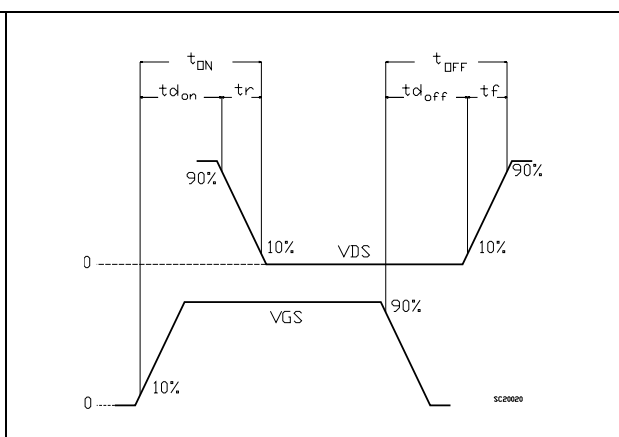


Figure 18. Switching time waveform

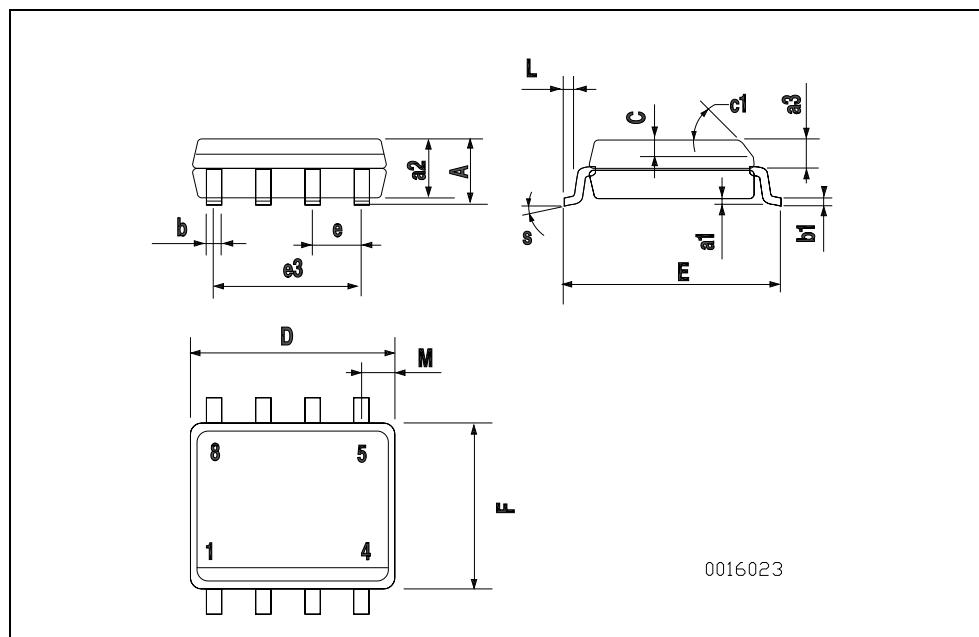


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : www.st.com

SO-8 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-----------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | | | 1.75 | | | 0.068 |
| a1 | 0.1 | | 0.25 | 0.003 | | 0.009 |
| a2 | | | 1.65 | | | 0.064 |
| a3 | 0.65 | | 0.85 | 0.025 | | 0.033 |
| b | 0.35 | | 0.48 | 0.013 | | 0.018 |
| b1 | 0.19 | | 0.25 | 0.007 | | 0.010 |
| C | 0.25 | | 0.5 | 0.010 | | 0.019 |
| c1 | 45 (typ.) | | | | | |
| D | 4.8 | | 5.0 | 0.188 | | 0.196 |
| E | 5.8 | | 6.2 | 0.228 | | 0.244 |
| e | | 1.27 | | | 0.050 | |
| e3 | | 3.81 | | | 0.150 | |
| F | 3.8 | | 4.0 | 0.14 | | 0.157 |
| L | 0.4 | | 1.27 | 0.015 | | 0.050 |
| M | | | 0.6 | | | 0.023 |
| S | 8 (max.) | | | | | |



0016023

5 Revision history

Table 7. Revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 11-Sep-2006 | 8 | Complete document |
| 15-Nov-2006 | 9 | The document has been reformatted |
| 30-Jan-2007 | 10 | Typo mistake on Table 1 . |

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